



PRODUCT DATA SHEET



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Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

Features

- 150Watts peak pulse power ($t_p = 8/20\mu s$)
- SOT23-6 package
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance ($C_j=0.3pF$ typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2 $\geq 12kV$ contact $\geq 5kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20 μs)



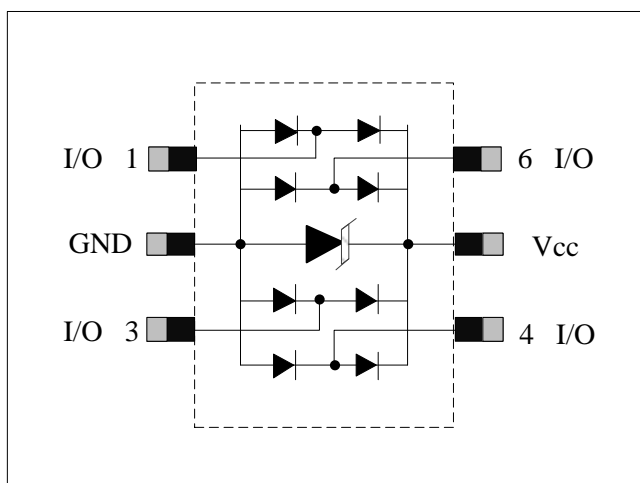
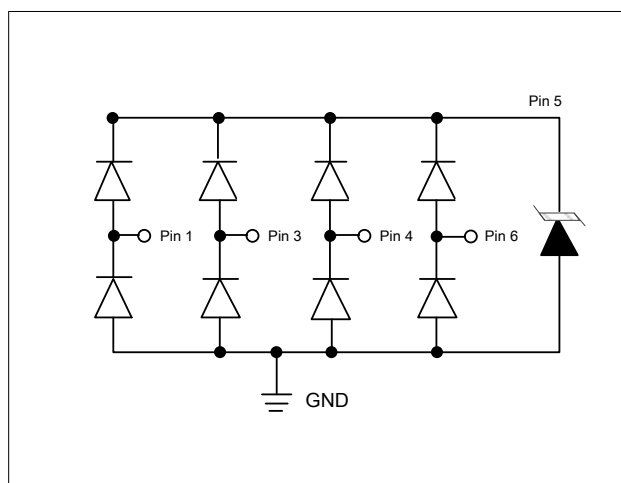
Applications

- Ethernet
- Digital Visual Interface (DVI)
- USB2.0
- Notebook and PC Computers

Mechanical Data

- SOT23-6 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Schematic & PIN Configuration



Absolute Maximum Rating

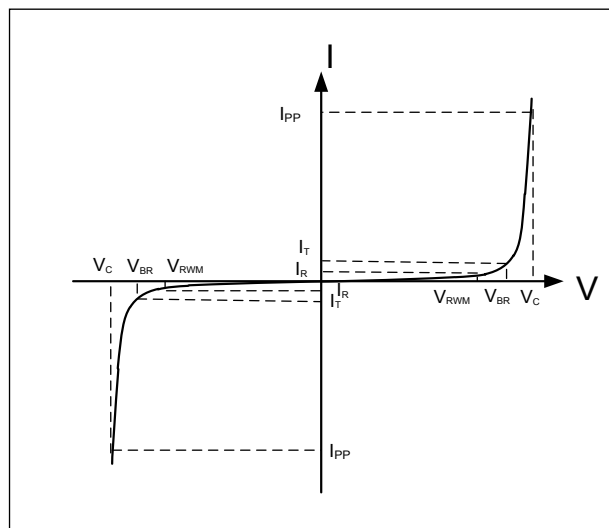
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20's$)	P_{PP}	150	Watts
Peak Pulse Current ($t_p = 8/20's$) (note1)	I_{pp}	5.0	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	15 12	kV
Lead Soldering Temperature	T_L	260(10seconds)	°C
Junction Temperature	T_J	-55 to + 125	°C
Storage Temperature	T_{stg}	-55 to + 125	°C

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	6			V
Reverse Leakage Current	I_R	$V_{RWM} = 5V, T = 25^{\circ}C$			1.0	uA
Peak Pulse Current	I_{PP}	$t_p = 8/20's$			5.0	A
Clamping Voltage	V_C	$I_{PP} = 5.0A, t_p = 8/20's$			16	V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$ IO to IO		0.3	0.45	pF
		$V_R = 0V, f = 1MHz$ IO to GND		0.6	0.9	

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Ver.1.0

Typical Characteristic Curves

Fig.1 Peak Pulse Power Rating Curve

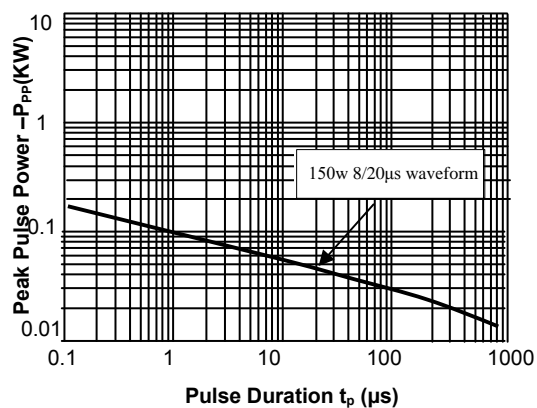


Fig.2 Pulse Derating Curve

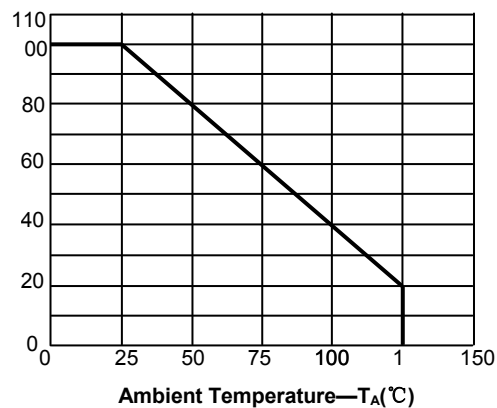


Fig.3 Pulse Waveform-8/20μs

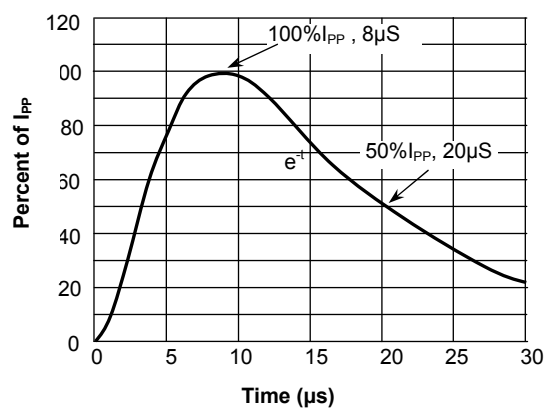
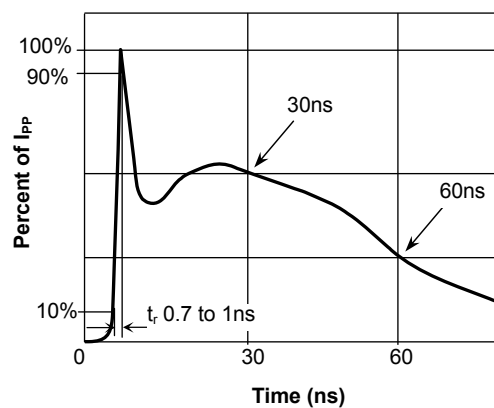
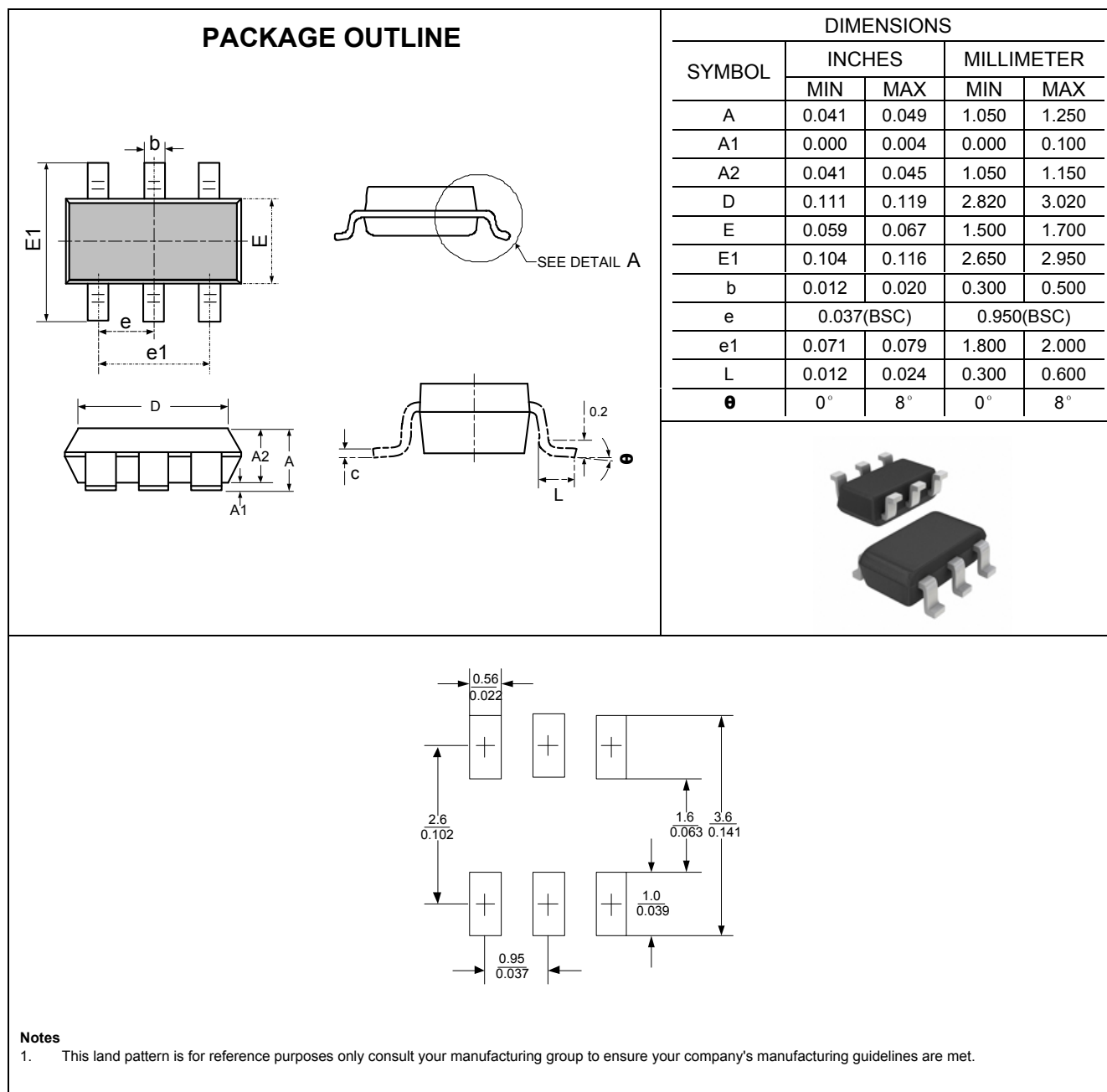


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)



Outline Drawing – SOT23-6



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